

**AMENDMENTS TO THE SPECIFICATION**

Please amend the title of the present application from “TEMPERATURE INDEPENDENT MICROELECTROMECHANICAL SWITCHES” to “MEMBRANE SWITCH COMPONENTS AND DESIGNS.”

Please replace the paragraph beginning on page 7, line 6 of the original Application with the following paragraph:

--“The modified fixed-free micromechanical beam (cantilever) 100 comprises a suspended beam 101, a mechanical anchor 102, a substrate 103, a control electrode 108, and a tether 107. The suspended beam 101 is connected on one end to the mechanical post 102, which rests upon the substrate 103. A control electrode 108 also rests upon the substrate 103, and is utilized to modify the position of the suspended beam 101. In the case of an electrostatically operated RF switch, an applied voltage is applied to control electrode 108 to move the suspended beam 101 into an alternative position or state. Accordingly, there is also a tether 107 attached between the substrate 103 and the suspended beam 101. ~~In some embodiments, a dielectric insulation layer 105 resides on the control electrode 108. The dielectric layer 105 could comprise Silicon Oxide ( $\text{SiO}_2$ ) or Silicon Nitride ( $\text{Si}_3\text{N}_4$ ).~~” —

Please replace the paragraph beginning on page 8, line 10 of the original Application with the following paragraph:

--“The modified fixed-fixed micromechanical structure 200 comprises a suspended beam 207, mechanical anchors 205, a substrate 201, a control electrode 202, and auxiliary beam springs 206.

The mechanical anchors 205 and the control electrode 202 rest on the substrate 201. The suspended beam 207 is attached to the beam springs 206, which flex and attempt to make contact with the control electrode when the beam is engaged. The beam springs 206 rest on and are attached to the mechanical anchors 205. The beam springs 206 are treated in detail below. ~~In some embodiments, a dielectric insulation layer 203 resides on the control electrode 202. The dielectric layer could comprise Silicon Oxide ( $\text{SiO}_2$ ) or Silicon Nitride ( $\text{Si}_3\text{N}_4$ ).~~—